

# HiPerDynFRED™ Epitaxial Diode

## ISOPLUS220™

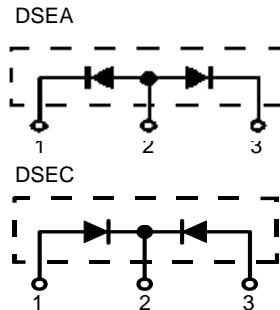
Electrically Isolated Back Surface

$$I_{FAV} = 2 \times 8 \text{ A}$$

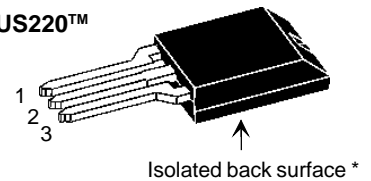
$$V_{RRM} = 600 \text{ V}$$

$$t_{rr} = 35 \text{ ns}$$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
600	600	DSEA 16-06AC
600	600	DSEC 16-06AC



ISOPLUS220™



\* Patent pending

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		35	A
$I_{FAVM}$	$T_C = 120^\circ\text{C}$ ; rectangular, $d = 0.5$	8	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	50	A
$E_{AS}$	$T_{VJ} = 25^\circ\text{C}$ ; non-repetitive $I_{AS} = 0.9 \text{ A}$ ; $L = 180 \mu\text{H}$	0.1	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_R$ typ.; $f = 10 \text{ kHz}$ ; repetitive	0.1	A
$T_{VJ}$		-55...+175	$^\circ\text{C}$
$T_{VJM}$		175	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	260	$^\circ\text{C}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	50	W
$V_{ISOL}$	50/60 Hz RMS; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
$F_C$	mounting force with clip	11...65 / 2.5...15	N / lb
Weight	typical	2	g

### Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low cathode to tab capacitance (<15pF)
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

### Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{RM}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

See DSEC 16-06A data sheet for characteristic curves.

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = V_{RRM}$		60 $\mu\text{A}$ 0.25 mA
$V_F$ ②	$I_F = 10 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$		1.42 V 2.10 V
$R_{thJC}$ $R_{thCH}$		0.6	3 K/W K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 50 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	35	ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 12 \text{ A}$ ; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	3.5	4.4 A

 Notes: Data given for  $T_{VJ} = 25^\circ\text{C}$  and per diode unless otherwise specified

① Pulse test: pulse Width = 5 ms, Duty Cycle &lt; 2.0 %

 ② Pulse test: pulse Width = 300  $\mu\text{s}$ , Duty Cycle < 2.0 %

IXYS reserves the right to change limits, test conditions and dimensions.

ISOPLUS220 OUTLINE

